

Ce Bian

List of Publications by Year in descending order

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11
papers

400
citations

1040056

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times ranked

672
citing authors

#	ARTICLE	IF	CITATIONS
1	Atomically sharp interface enabled ultrahigh-speed non-volatile memory devices. <i>Nature Nanotechnology</i> , 2021, 16, 882-887.	31.5	105
2	Quasi-2D Transport and Weak Antilocalization Effect in Few-layered VSe_2 . <i>Nano Letters</i> , 2019, 19, 4551-4559.	9.1	60
3	Observation of the Kondo Effect in Multilayer Single-Crystalline VTe_2 Nanoplates. <i>Nano Letters</i> , 2019, 19, 8572-8580.	9.1	52
4	InSe/hBN/graphite heterostructure for high-performance 2D electronics and flexible electronics. <i>Nano Research</i> , 2020, 13, 1127-1132.	10.4	48
5	Epitaxial growth of metal-semiconductor van der Waals heterostructures NbS_2/MoS_2 with enhanced performance of transistors and photodetectors. <i>Science China Materials</i> , 2020, 63, 1548-1559.	6.3	40
6	Assembly of hard spheres in a cylinder: a computational and experimental study. <i>Soft Matter</i> , 2017, 13, 3296-3306.	2.7	29
7	Ultrathin FeTe nanosheets with tetragonal and hexagonal phases synthesized by chemical vapor deposition. <i>Materials Today</i> , 2021, 45, 35-43.	14.2	29
8	Transition-Metal Substitution-Induced Lattice Strain and Electrical Polarity Reversal in Monolayer WS_2 . <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 18650-18659.	8.0	20
9	Reversible Modification of Nitrogen-Doped Graphene Based on Se-N Dynamic Covalent Bonds for Field-Effect Transistors. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 24360-24366.	8.0	13
10	Substrate, a choice of engineering the pseudospin in graphene. <i>2D Materials</i> , 2019, 6, 045050.	4.4	4
11	One-dimensional weak antilocalization effect in $1T'-MoTe_2$ nanowires grown by chemical vapor deposition. <i>Journal of Physics Condensed Matter</i> , 2021, 33, 185701.	1.8	0